

01/12/2006

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

Homogeneous Copper Interconnects for BEOL

Application Number :

Confirmation Number:

First Named Applicant: Kevin Petrarca

Attorney Docket Number: FIS920040258US1

Art Unit:

Examiner:

Search string: (6709562 or 6380628 or 6339258 or 6337151 or 6743719 or 6472023 or 6680514 or 6071814 or 6136707 or 6174799 or 6368961 or 6726535 or 20040021226 or 20020027082).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
THN	1	6709562	2004-03-23	ANDRICACOS, ET AL.			
THN	2	6380628	2002-04-30	MILLER, ET AL.			
THN	3	6339258	2002-01-15	COONEY, III, ET AL.			
THN	4	6337151	2002-01-08	UZOH, ET AL.			
THN	5	6743719	2004-06-01	CHEN, ET AL.			
THN	6	6472023	2002-10-29	WU, ET AL.			
THN	7	6680514	2004-01-20	GEFFKEN, ET AL.			
THN	8	6071814	2000-06-06	JANG			
THN	9	6136707	2000-10-24	COHEN			
THN	10	6174799	2001-01-16	LOPATIN, ET AL.			
THN	11	6368961	2002-04-09	LOPATIN, ET AL.			
THN	12	6726535	2004-04-27	SHIH, ET AL.			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

Shan L. Zyl


09/13/06

01/17/2006

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

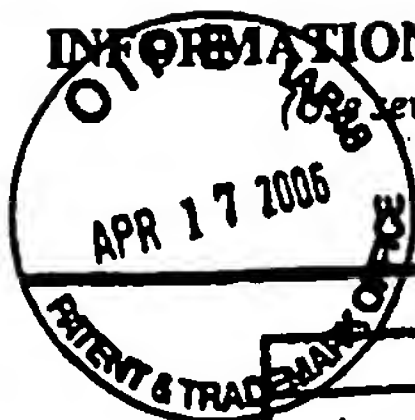
Electronic Version v18

Stylesheet Version v18.0

Title of Invention	HOMOGENEOUS COPPER INTERCONNECTS FOR BEOL						
<div>Application Number : 10/711700</div> <div>Confirmation Number: 5699</div> <div>First Named Applicant: Kevin Petrarca</div> <div>Attorney Docket Number: FIS920040258US1</div> <div>Art Unit: 2811</div> <div>Examiner:</div> <div>Search string: (5969422 or 6350688).pn</div> <div></div>							
<p>Certification: This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:</p> <p>That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement.</p>							
US Patent Documents							
Note: Applicant is not required to submit a paper copy of cited US Patent Documents							
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
THN	1	5969422	1999-10-19	TING, ET AL.			
THN	2	6350688	2002-02-26	LIU, ET AL.			
Signature							
Examiner Name				Date			
Dean Li				09/13/2006			

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)
FIS920040258US1

Application Number
10/711,700

Applicant(s)
Kevin Petrarca, et al.

Filing Date
09/30/04

Group Art Unit
2818

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
THN	AA**	US-5,484,518	01/1996	GOLDBERG	
THN	AB**	US-6,261,433	07/2001	LANDAU	
THN	AC**	US-6,331,237	12/2001	ANDRICACUS et al.	
THN	AD**	US-6,113,771	09-05-2000	LANDAU et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T*
THN	BA**	EP-0952242	11-16-1998	LANDAU, et al.		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. **CITE NO.: Those patent(s) or publication(s) which are marked with an double asterisk (**) next to the Cite No. are not supplied because they were previously cited by or submitted to the Office in a prior application relied upon in this application for an earlier filing date under 35 U.S.C. 120. ¹ Applicant's unique citation designation number (optional). ² See Kind's Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
THN	CA**	A Novel Electrolyte Composition for Copper Plating in Wafer Metallization, Electrochemical Processing in ULSI Fabrication and Semiconductor/Metal Deposition II: Proceedings of the International Symposium; P.C.: Uziel LANDAU, et al., The Electrochemical Society, Inc. Proceedings Volume 99-9.	
THN	CB**	A Model of Superfilling in Damascene Electroplating, H. DELIGIANNI, et al.; The 195 th Meeting of Electrochemical Society, Inc. Meeting Abstracts, Volume 99-1 (May 2-6, 1999).	
THN	CC**	Model of Wafer Thickness Uniformity in an Electroplating Tool, The 195 th Meeting of Electrochemical Society, Inc. Meeting Abstracts, Volume 99-1 (May 2-6, 1999).	
THN	CD**	A Model of Superfilling in Damascene Electroplating, H. DELIGIANNI, et al.; Electrochemical Processing in ULSI Fabrication and Semiconductor/Metal Deposition II: Proceedings of the International Symposium; P.C.: Uziel LANDAU, et al., The Electrochemical Society, Inc., Proceedings Volume 99-9.	
THN	CE**	Uziel LANDAU, A Novel Electrolyte Composition for Copper Plating in Wafer Metallization, Abstract No. 263.	
THN	CF**	Model of Wafer Thickness Uniformity in an Electroplating Tool, Electrochemical Processing in ULSI Fabrication and Semiconductor/Metal Deposition II: Proceedings of the International Symposium; P.C.H. DELIGIANNI, et al., The Electrochemical Society, Inc., Proceedings Volume 99-9.	
THN	CG**	Computational Aspects of the Terminal Effect on Wafer-Scale Uniformity, H. DELIGIANNI et al.; The 195 th Meeting of Electrochemical Society, Inc. Meeting Abstracts, Volume 99-1 (May 2-6, 1999).	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. **CITE NO.: Those patent(s) or publication(s) which are marked with an double asterisk (**) next to the Cite No. are not supplied because they were previously cited by or submitted to the Office in a prior application relied upon in this application for an earlier filing date under 35 U.S.C. 120.

Examiner Signature	<i>[Signature]</i>	Date Considered	07/06/06
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